

**Notice of References Cited**

Applicant/Patent

Ahn et al.

Application/Control No.

09/755,071

Examiner

George C. Eckert II

Art Unit

2815

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**NON-PATENT DOCUMENTS**

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
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<sup>\*</sup> A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).<sup>1</sup> Dates in MM-YYYY format are publication dates.<sup>2</sup> Classifications may be U.S. or foreign.